

# Nanoobjects microscopy

## Nanoscale 3d visualization of grain boundaries

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A new technique of field ion grain boundary 3d study on nanoscale level is presented. This method is characterized by a comparatively low field strength due to the presence of water vapor at the room temperature. Image forming in described here a low field technique is based on phenomenon of field desorption stimulated by surface chemical reaction. The emission occurs in field strength  $2.8 > F \geq 0.4$  V/nm with permanent field evaporation, with maximum rate along sample axis about 20 nm/s. Image is formed in two modes:  $0.4 \div 1.6$  V/nm – dynamic mode and  $1.6 \div 2.8$  V/nm – cross-shaped mode; both are named after image character. The magnification in modes is about  $10^4$ . In dynamic mode image is formed by spots with a size  $\sim 50$  nm[1]. Such resolution restriction allows to solve material science problems such as grain boundaries spatial grid and triple junction determination.

Constant evaporation rate in a W-20%Re alloy dynamic mode allows to obtain step-by-step grain boundaries images. Those images can be used for creating a 3d video model to observe and study grain boundaries structure in a volume ( $1 \times 1 \times 2,5$  mkm<sup>3</sup>). Fig. 1 shows a base sample (a) and 3 perpendicular cross-sections images (b, c, d).

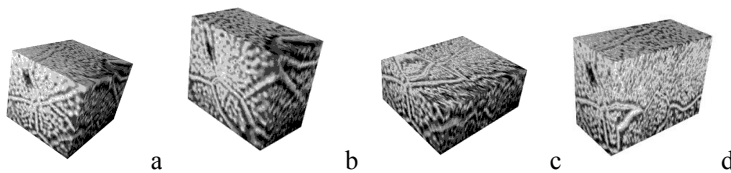


Fig. 1

Investigation of grain boundary structure in a grain-oriented W-20%Re alloy has shown the presence of twist boundaries segments mainly near triple junctions. Such grain boundaries were generated by the  $\{110\}$  planes rotated about the texture axis.

1. Ksenofontov V. A., Sadanov E. V., Velikodnaja O. A. Low-field ion microscopy // TechPhys.-2009.-54, N 4.-P. 580-585.